

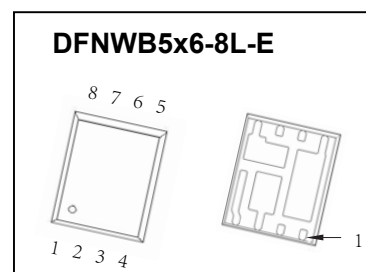


JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

DFNWB5×6-8L-E Plastic-Encapsulate MOSFETS

CJFB30H20 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	8.5mΩ@10V	20A
	12mΩ@4.5V	



DESCRIPTION

The CJFB30H20 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

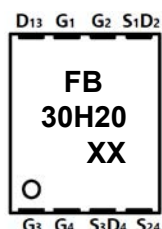
FEATURES

- Full Bridge switch
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

APPLICATIONS

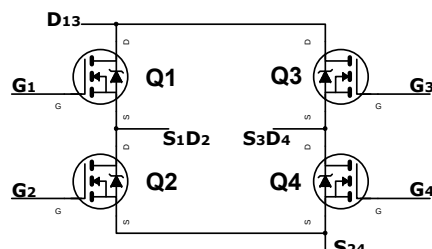
- SMPS and general purpose applications
- Hard switched and high frequency circuits

MARKING



FB30H20 = Part No.
Solid dot = Pin1 indicator.
XX = Code.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	20	A
Pulsed Drain Current	I_{DM}	100	A
Single Pulsed Avalanche Energy	$E_{AS}^{(1)}$	70	mJ
Power Dissipation	P_D	1.5	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	83.3	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ +150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T_L	260	$^{\circ}\text{C}$

(1).EAS condition: $V_{DD}=15V, L=0.14mH, R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

(2).Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

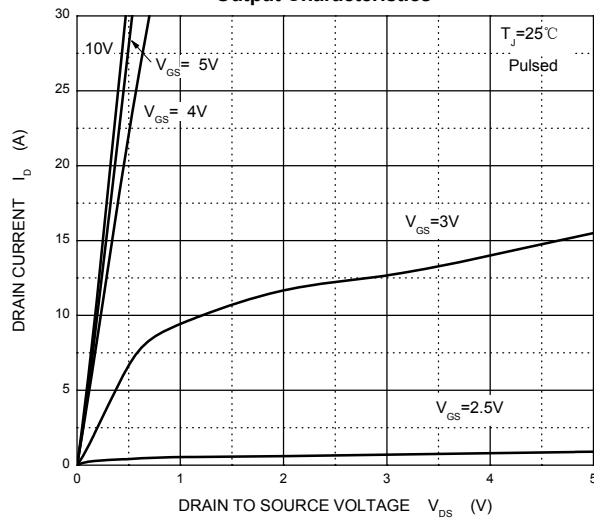
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
On characteristics (note1)						
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.7	3.0	V
Static drain-source on-sate resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A		8.5	12	mΩ
		V _{GS} =4.5V, I _D =10A		12	18	mΩ
Forward transconductance	g _{FS}	V _{DS} =5V, I _D =20A	15			S
Dynamic characteristics (note 2)						
Input capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V, f =1MHz		823		pF
Output capacitance	C _{oss}			138		
Reverse transfer capacitance	C _{rss}			100		
Switching characteristics (note 2)						
Total gate charge	Q _g	V _{DS} =15V, V _{GS} =10V, I _D =9A		13		nC
Gate-source charge	Q _{gs}			3		
Gate-drain charge	Q _{gd}			4.5		
Turn-on delay time	t _{d(on)}	V _{DS} =15V,V _{GS} =10V, R _L =1.8Ω,R _{GEN} =3Ω			10	ns
Turn-on rise time	t _r				8	
Turn-off delay time	t _{d(off)}				30	
Turn-off fall time	t _f				5	
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note1)	V _{SD}	V _{GS} =0V, I _S =10A			1.2	V
Continuous drain-source diode forward current	I _S				20	A
Pulsed drain-source diode forward current	I _{SM}				100	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 10A		22	35	ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs(Note1)		12	20	nC

Notes:

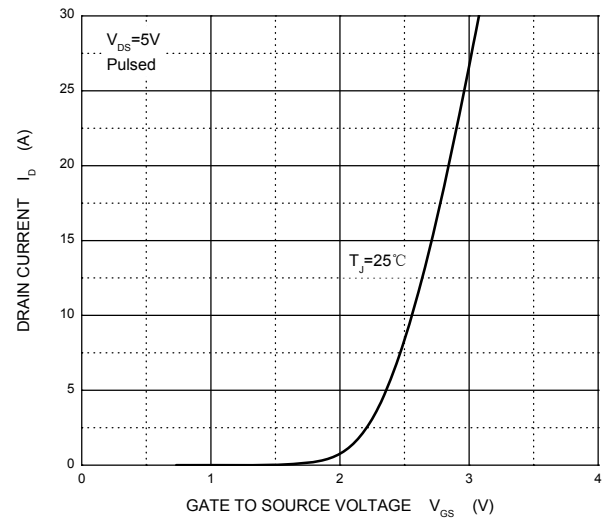
1. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production.

Typical Characteristics

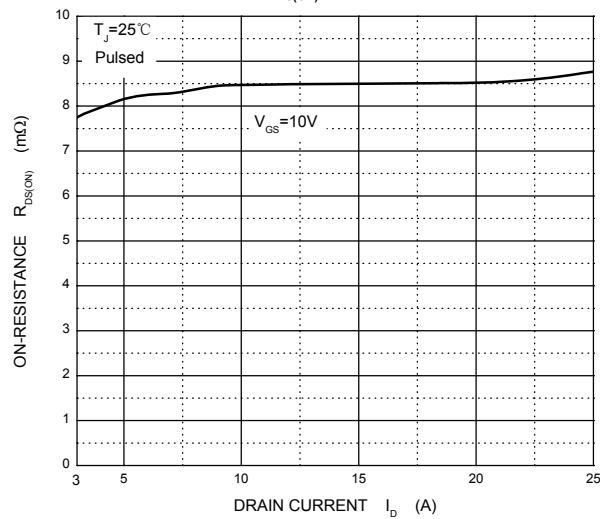
Output Characteristics



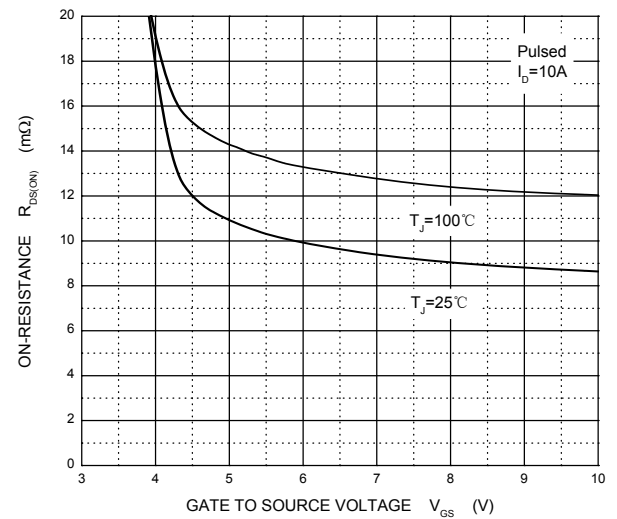
Transfer Characteristics



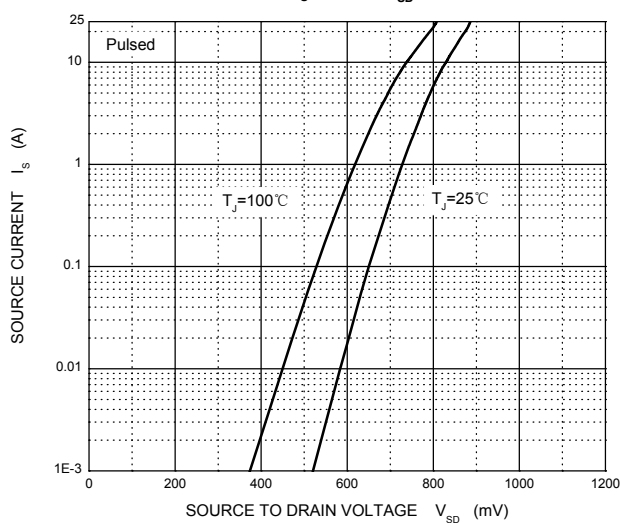
$R_{DS(ON)}$ — I_D



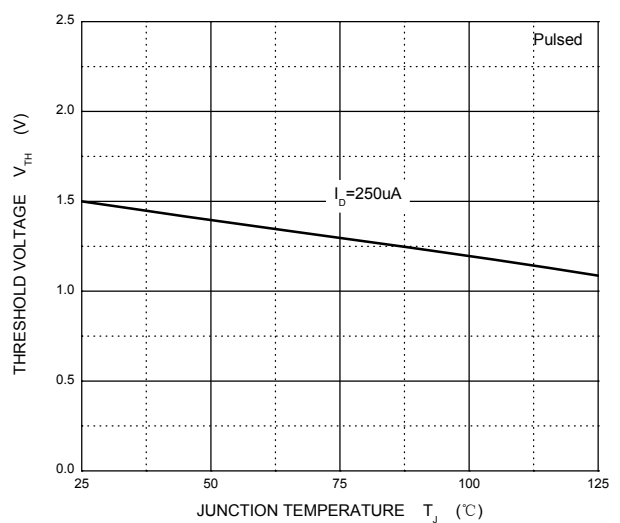
$R_{DS(ON)}$ — V_{GS}

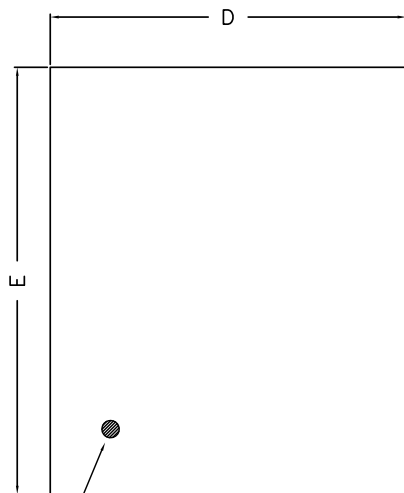


I_S — V_{SD}

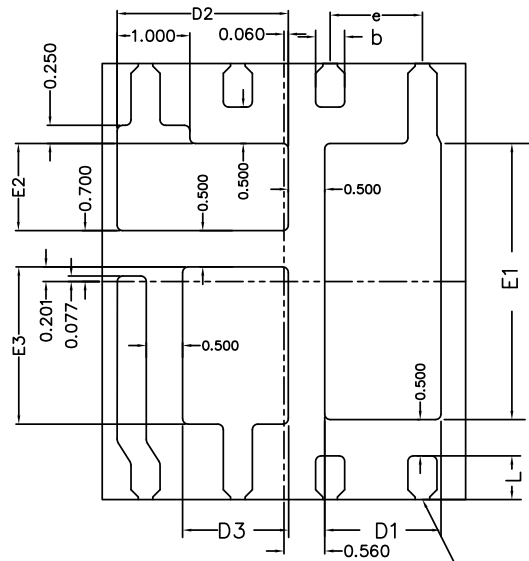


Threshold Voltage



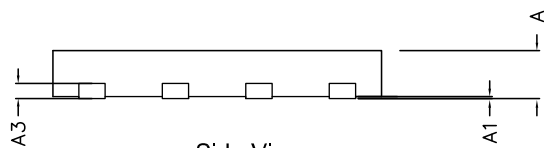


Top View
[顶视图]



Bottom View
[背视图]

PIN #1 LOCATION



Side View
[侧视图]

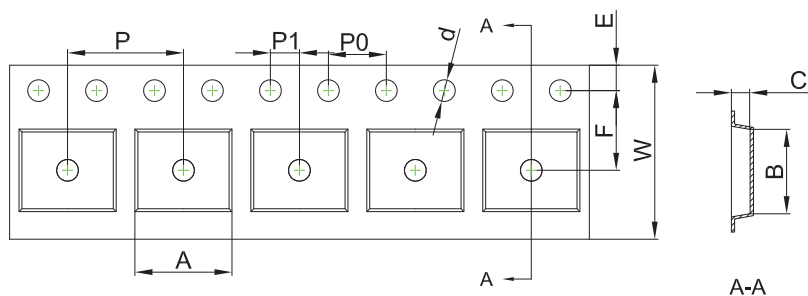
COMMON DIMENSIONS(MM)			
PKG.	W:VERY VERY THIN		
REF.	MIN.	NOM.	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.2 REF.		
D	4.90	5.00	5.10
E	5.90	6.00	6.10
b	0.35	0.40	0.45
L	0.50	0.60	0.70
D1	1.35	1.60	1.70
E1	3.65	3.80	3.90
D2	2.205	2.355	2.455
E2	1.05	1.20	1.30
D3	1.305	1.455	1.555
E3	2.013	2.163	2.263
e	1.27 BSC		

NOTICE

JSCJ reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

DFNWB5x6-8L-E Tape and Reel

DFNWB5x6-8L-E Embossed Carrier Tape



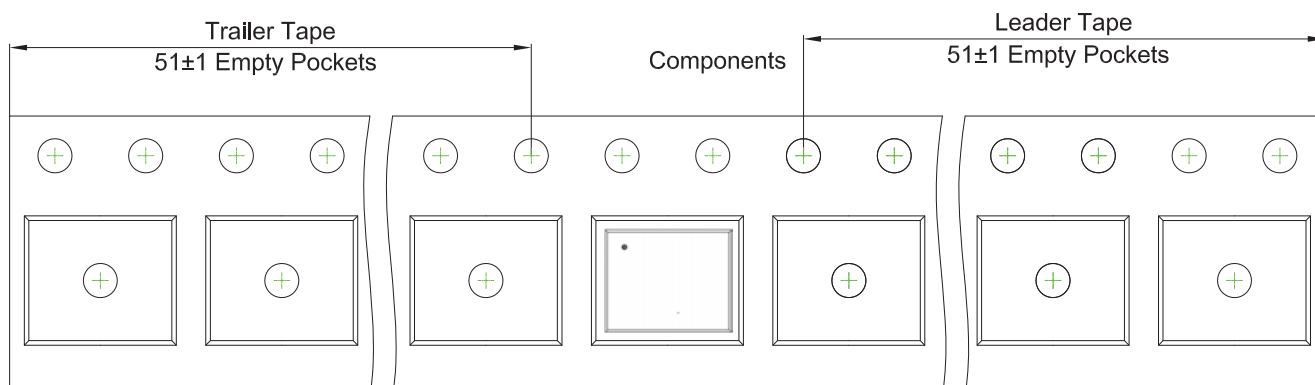
Packaging Description:

DFNWB5x6-8L-E parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

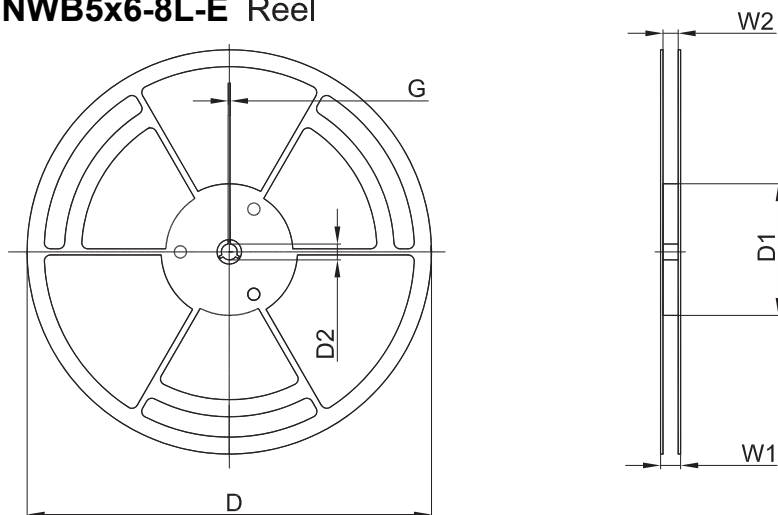
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
DFNWB5x6-8L-E	6.30	5.30	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

DFNWB5x6-8L-E Tape Leader and Trailer



DFNWB5x6-8L-E Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365